	Application No.	Applicant(s)
	09/428,052	IRINO, KIYOSHI
	Examiner	Art Unit
	José R. Díaz	2815
The MAILING DATE of this communication appea All claims being allowable, PROSECUTION ON THE MERITS IS (0 herewith (or previously mailed), a Notice of Allowance (PTOL-85) o NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIG of the Office or upon petition by the applicant. See 37 CFR 1.313 a	OR REMAINS) CLOSED in other appropriate comministry. This application is	n this application. If not included nunication will be mailed in due course. <b>THIS</b>
1. ☑ This communication is responsive to <u>8/1/05</u> .		
2. $\boxtimes$ The allowed claim(s) is/are <u>6</u> .		
<ol> <li>Acknowledgment is made of a claim for foreign priority und</li> <li>a) ☐ All b) ☐ Some* c) ☐ None of the:</li> <li>1. ☐ Certified copies of the priority documents have be</li> </ol>		or (f).
2.   Certified copies of the priority documents have to	peen received in Applicati	on No. <u>08/917,936</u> .
3.  Copies of the certified copies of the priority docu	ıments have been receive	ed in this national stage application from the
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONME THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the requirements
<ol> <li>A SUBSTITUTE OATH OR DECLARATION must be submitt INFORMAL PATENT APPLICATION (PTO-152) which gives</li> </ol>	ed. Note the attached EX reason(s) why the oath c	AMINER'S AMENDMENT or NOTICE OF or declaration is deficient.
5. CORRECTED DRAWINGS ( as "replacement sheets") must	be submitted.	
(a) including changes required by the Notice of Draftsperso	n's Patent Drawing Revie	w ( PTO-948) attached
1)  hereto or 2)  to Paper No./Mail Date		
(b) including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment o	or in the Office action of
Identifying indicia such as the application number (see 37 CFR 1.8 each sheet. Replacement sheet(s) should be labeled as such in the	4(c)) should be written on t e header according to 37 C	the drawings in the front (not the back) of FR 1.121(d).
6. DEPOSIT OF and/or INFORMATION about the deposi attached Examiner's comment regarding REQUIREMENT For	It of BIOLOGICAL MAT OR THE DEPOSIT OF BI	ERIAL must be submitted. Note the OLOGICAL MATERIAL.
Attachment(s)	C [ N-Aire of l	of and Detect Application (DTO 150)
1. Notice of References Cited (PTO-892)		nformal Patent Application (PTO-152) Summary (PTO-413),
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	Paper No	./Mail Date
3. Information Disclosure Statements (PTO-1449 or PTO/SB/08	), 7. 🛭 Examiner's	Amendment/Comment
Paper No./Mail Date  4.  Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. 🛭 Examiner's	s Statement of Reasons for Allowance
	9. 🗌 Other	
		comerd / man
		SARAHERATE
	SIF	Tom Thomas Envisory patent examiner

## **EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Stephen Adrian on September 22, 2005.

The application has been amended as follows:

Please delete the phrase "after introducing N atoms to said gate oxide film" in the limitation beginning with "said thermal annealing process being conducted at a temperature of about 800 °C over a duration of 5 minutes or more..."

## **REASONS FOR ALLOWANCE**

2. The following is an examiner's statement of reasons for allowance: the prior art fails to teach, disclose, or suggest, either alone or in combination, a method of fabricating a semiconductor device comprising the steps of thermal annealing said gate oxide film at a temperature of 800 °C over a duration of at least 5 minutes such that N atoms are concentrated at an interface between the substrate and the gate oxide film; CVD depositing an oxide film on said gate oxide, wherein the steps of introducing N atoms and CVD depositing the oxide film are conducted consecutively in a common processing chamber, without taking out the substrate into an atmospheric environment as instantly claimed, and in combination with the additional method steps.

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Any comments considered necessary by applicant must be submitted no later

than the payment of the issue fee and, to avoid processing delays, should preferably

accompany the issue fee. Such submissions should be clearly labeled "Comments on

Statement of Reasons for Allowance."

Correspondence

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to José R. Díaz whose telephone number is (571) 272-

1727. The examiner can normally be reached on Monday through Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number

for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for

published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only.

For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

José R. Díaz Examiner

Art Unit 2815

(pm /Nome

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SUPERVISORY PATENT EL